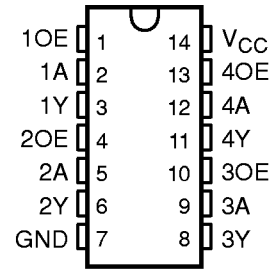


# SN74ALVC126 QUADRUPLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES111E – JULY 1997 – REVISED FEBRUARY 1999

- **EPIC™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (D), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

D, DGV, OR PW PACKAGE  
(TOP VIEW)



## description

This quadruple bus buffer gate is designed for 1.65-V to 3.6-V  $V_{CC}$  operation.

The SN74ALVC126 features independent line drivers with 3-state outputs. Each output is disabled when the associated output-enable (OE) input is low.

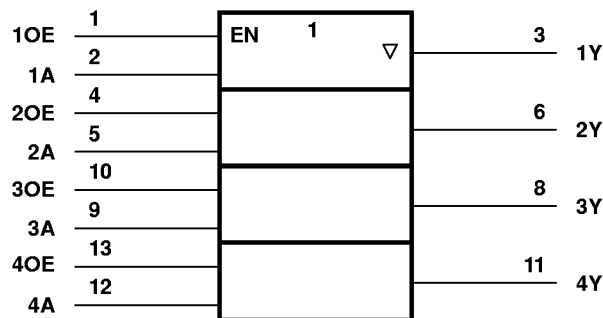
To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pull-down resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

The SN74ALVC126 is characterized for operation from  $-40^{\circ}\text{C}$  to  $85^{\circ}\text{C}$ .

**FUNCTION TABLE**  
(each buffer)

INPUTS		OUTPUT
OE	A	Y
H	H	H
H	L	L
L	X	Z

## logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



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**recommended operating conditions (see Note 4)**

		MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage	1.65	3.6	V
V <sub>IH</sub>	High-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	
		V <sub>CC</sub> = 2.7 V to 3.6 V	2	
V <sub>IL</sub>	Low-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	0.7	
		V <sub>CC</sub> = 2.7 V to 3.6 V	0.8	
V <sub>I</sub>	Input voltage	0	V <sub>CC</sub>	V
V <sub>O</sub>	Output voltage	0	V <sub>CC</sub>	V
I <sub>OH</sub>	High-level output current	V <sub>CC</sub> = 1.65 V	-4	mA
		V <sub>CC</sub> = 2.3 V	-12	
		V <sub>CC</sub> = 2.7 V	-12	
		V <sub>CC</sub> = 3 V	-24	
I <sub>OL</sub>	Low-level output current	V <sub>CC</sub> = 1.65 V	4	mA
		V <sub>CC</sub> = 2.3 V	12	
		V <sub>CC</sub> = 2.7 V	12	
		V <sub>CC</sub> = 3 V	24	
Δt/Δv	Input transition rise or fall rate		5	ns/V
T <sub>A</sub>	Operating free-air temperature	-40	85	°C

NOTE 4: All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V <sub>CC</sub>	MIN	TYP†	MAX	UNIT
V <sub>OH</sub>		I <sub>OH</sub> = -100 μA	1.65 V to 3.6 V	V <sub>CC</sub> -0.2			V
		I <sub>OH</sub> = -4 mA	1.65 V	1.2			
		I <sub>OH</sub> = -6 mA	2.3 V	2			
		I <sub>OH</sub> = -12 mA	2.3 V	1.7			
			2.7 V	2.2			
			3 V	2.4			
V <sub>OL</sub>		I <sub>OL</sub> = 100 μA	1.65 V to 3.6 V			0.2	V
		I <sub>OL</sub> = 4 mA	1.65 V			0.45	
		I <sub>OL</sub> = 6 mA	2.3 V			0.4	
		I <sub>OL</sub> = 12 mA	2.3 V			0.7	
			2.7 V			0.4	
			3 V			0.55	
I <sub>I</sub>		V <sub>I</sub> = V <sub>CC</sub> or GND	3.6 V			±5	μA
I <sub>OZ</sub>		V <sub>O</sub> = V <sub>CC</sub> or GND	3.6 V			±10	μA
I <sub>CC</sub>		V <sub>I</sub> = V <sub>CC</sub> or GND, I <sub>O</sub> = 0	3.6 V			10	μA
ΔI <sub>CC</sub>		One input at V <sub>CC</sub> - 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 3.6 V			750	μA
C <sub>i</sub>	Control inputs	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V			3.5	pF
	Data inputs					3.5	
C <sub>o</sub>	Outputs	V <sub>O</sub> = V <sub>CC</sub> or GND	3.3 V			5.5	pF

† All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

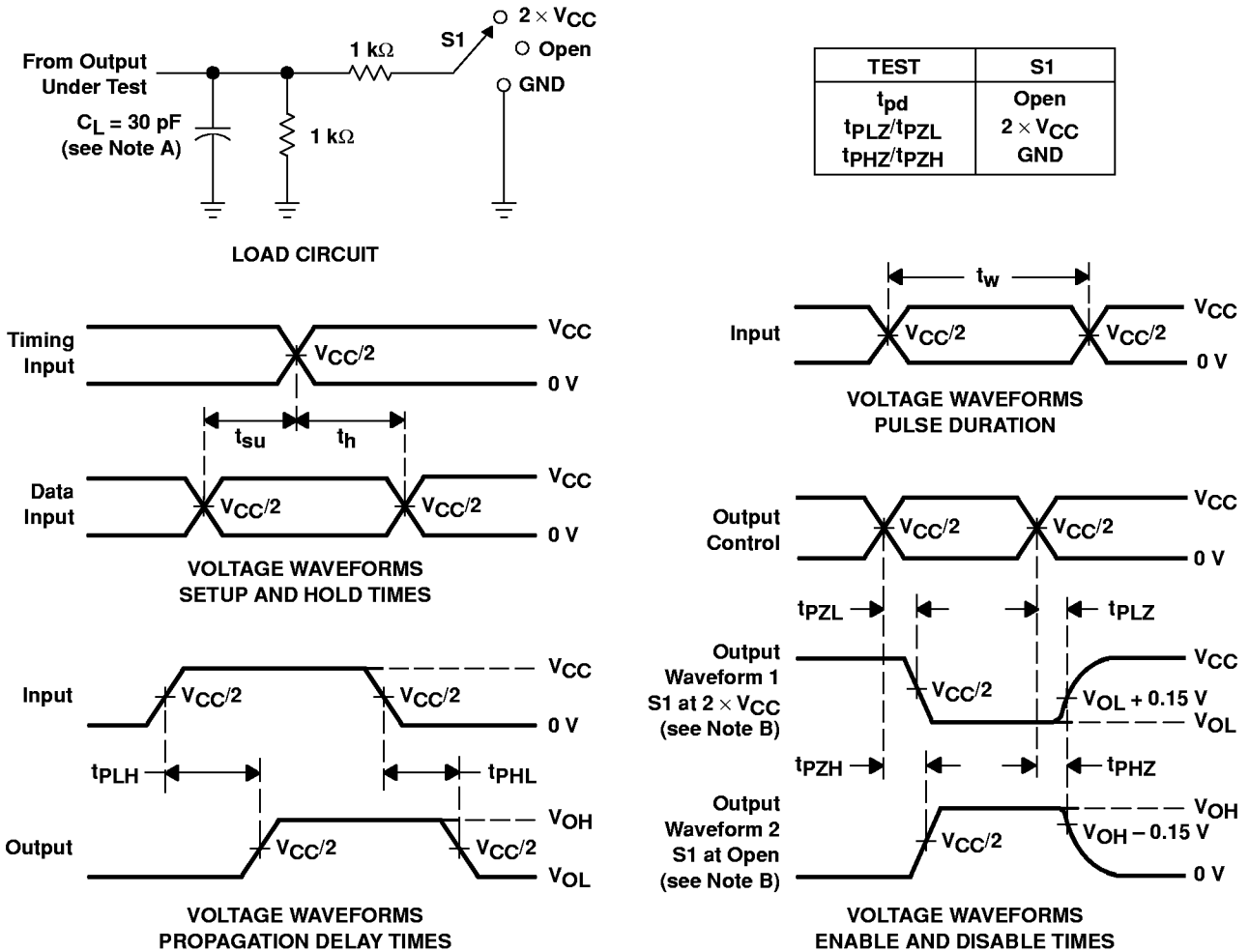
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1.8 V ± 0.15 V		V <sub>CC</sub> = 2.5 V ± 0.2 V		V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A	Y	1.3	5.6	1	3.4	3.4		1.1	3.1	ns
t <sub>en</sub>	OE	Y	1	5.9	1	3.8	3.8		1	3.3	ns
t <sub>dis</sub>	OE	Y	1.8	5.6	1	3.3	4.4		1	3.7	ns

operating characteristics, T<sub>A</sub> = 25°C

PARAMETER		TEST CONDITIONS	V <sub>CC</sub> = 1.8V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	UNIT	
			TYP	TYP	TYP		
C <sub>pd</sub>	Power dissipation capacitance per gate	Outputs enabled	C <sub>L</sub> = 0, f = 10 MHz	15	17	19	pF
		Outputs disabled		2	2	3	



**PARAMETER MEASUREMENT INFORMATION**  
 $V_{CC} = 1.8\text{ V} \pm 0.15\text{ V}$



- NOTES: A.  $C_L$  includes probe and jig capacitance.  
 B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.  
 C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2\text{ ns}$ ,  $t_f \leq 2\text{ ns}$ .  
 D. The outputs are measured one at a time with one transition per measurement.  
 E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .  
 F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .  
 G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

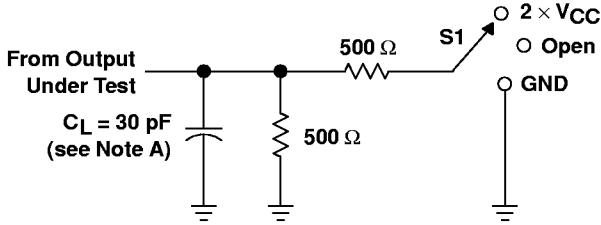
**Figure 1. Load Circuit and Voltage Waveforms**

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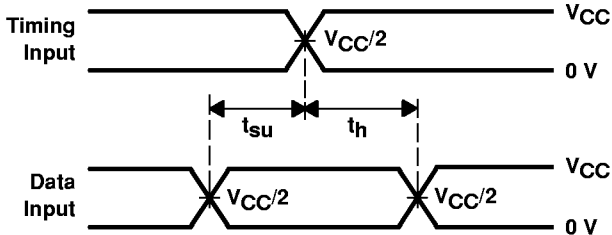
**PARAMETER MEASUREMENT INFORMATION**

$V_{CC} = 2.5\text{ V} \pm 0.2\text{ V}$

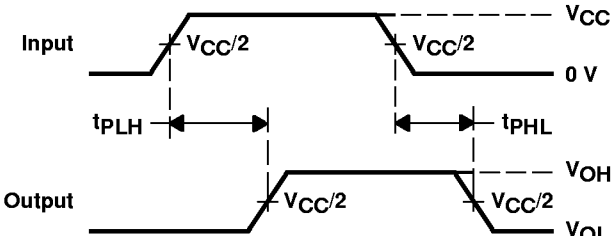


**LOAD CIRCUIT**

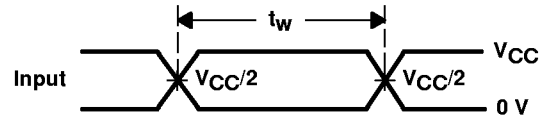
TEST	S1
$t_{pd}$	Open
$t_{pLZ}/t_{pZL}$	2 $\times V_{CC}$
$t_{PHZ}/t_{pZH}$	GND



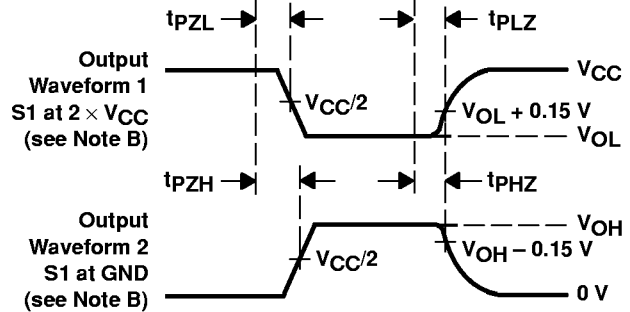
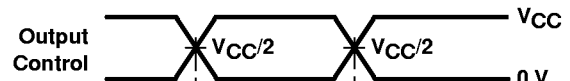
**VOLTAGE WAVEFORMS  
 SETUP AND HOLD TIMES**



**VOLTAGE WAVEFORMS  
 PROPAGATION DELAY TIMES**



**VOLTAGE WAVEFORMS  
 PULSE DURATION**

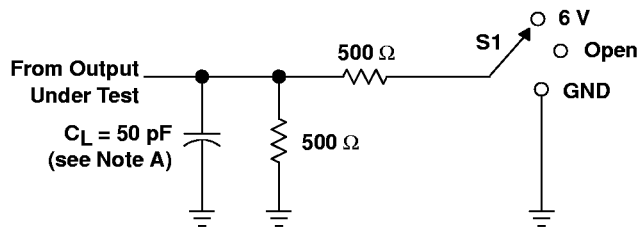


**VOLTAGE WAVEFORMS  
 ENABLE AND DISABLE TIMES**

- NOTES:
- A.  $C_L$  includes probe and jig capacitance.
  - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
  - C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2\text{ ns}$ ,  $t_f \leq 2\text{ ns}$ .
  - D. The outputs are measured one at a time with one transition per measurement.
  - E.  $t_{pLZ}$  and  $t_{pHZ}$  are the same as  $t_{dis}$ .
  - F.  $t_{pZL}$  and  $t_{pZH}$  are the same as  $t_{en}$ .
  - G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

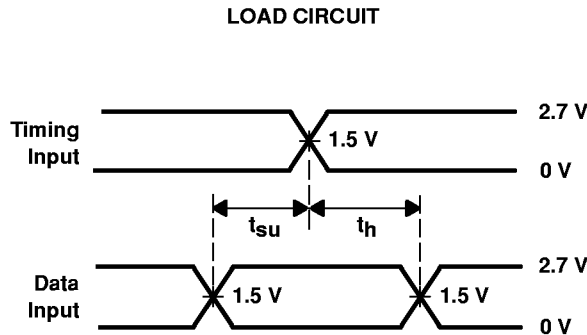
**Figure 2. Load Circuit and Voltage Waveforms**

PARAMETER MEASUREMENT INFORMATION  
 $V_{CC} = 2.7\text{ V}$  AND  $3.3\text{ V} \pm 0.3\text{ V}$

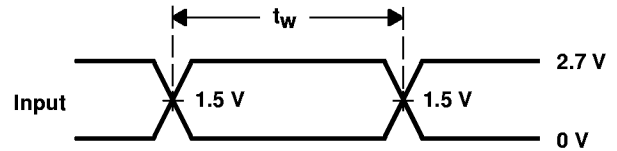


LOAD CIRCUIT

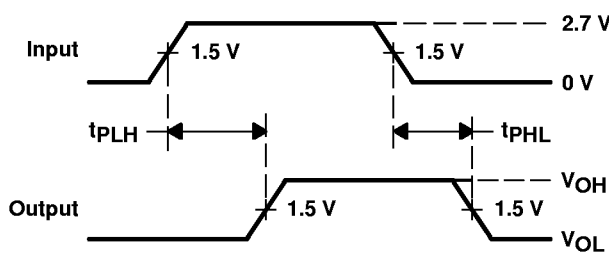
TEST	S1
$t_{pd}$	Open
$t_{PLZ}/t_{PZL}$	6 V
$t_{PHZ}/t_{PZH}$	GND



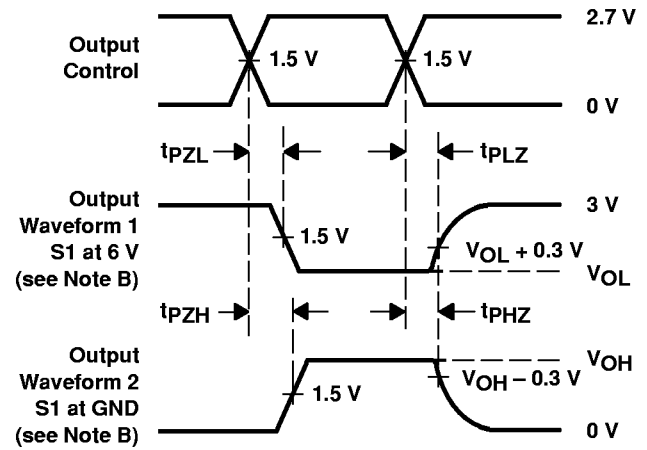
VOLTAGE WAVEFORMS  
 SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS  
 PULSE DURATION



VOLTAGE WAVEFORMS  
 PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS  
 ENABLE AND DISABLE TIMES

- NOTES:
- $C_L$  includes probe and jig capacitance.
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  - All input pulses are supplied by generators having the following characteristics:  $PRR \leq 10\text{ MHz}$ ,  $Z_O = 50\ \Omega$ ,  $t_r \leq 2.5\text{ ns}$ ,  $t_f \leq 2.5\text{ ns}$ .
  - The outputs are measured one at a time with one transition per measurement.
  - $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .
  - $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
  - $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

Figure 3. Load Circuit and Voltage Waveforms

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